

Acknowledgements

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Table of contents

| | |
|--|----|
| Chapter 1. Introduction | 1 |
| 1.1 Electro -optic and nonlinear optical properties of materials | 2 |
| 1.2 Electro -optic devices | 6 |
| 1.3 Objectives of research | 9 |
| 1.4 References | 12 |
| | |
| Chapter 2. Preparation and Optical Properties of III -V Semiconductor Nano -cluster and Polymeric Electro -optic Films | 15 |
| 2.1 Introduction | 15 |
| 2.1.1 General theories and concepts concerning semiconductor nano -crystals | 15 |
| 2.1.2 Preparing of Semiconductor nano -clusters | 22 |
| 2.2 Films preparing | 25 |
| 2.2.1 Electrostatic self -assembly (ESA) technique | 25 |
| 2.2.2 Spin coating of nano -particledoped polymeric EO films | 28 |
| 2.2.3 Poling of spinning coated electro -optic films | 29 |
| 2.3 Characterization of fabricated nano -clusters and -of films | 31 |
| 2.4 Experimental procedure | 32 |
| 2.4.1 III -V semiconductor nano -crystals and films preparation | 32 |
| 2.4.2 Preparing of electro -optic films by ESA technique | 33 |
| 2.4.3 Spin coating of nano -particledoped polymeric EO films | 34 |

| | |
|---|-----|
| 2.5 Results and discussion | 35 |
| 2.5.1 Absorption and PL spectra and nano -cluster synthesis | 35 |
| 2.5.2 Analysis of the shift of absorption spectra because of particle size | 44 |
| 2.5.3 Internal field of films induced by ESA process | 47 |
| 2.5.4 Comparison and process controlling of film growth by ESA technique | 54 |
| 2.5.5 Stability of nano -cluster and polymeric electro -optic films | 60 |
| 2.6 Conclusions | 65 |
| 2.7 References | 67 |
| | |
| Chapter 3. Electro -optic Properties of II -VI Semiconductor Nano -clusters and Electro - optic Chromophores | 69 |
| 3.1 Introduction | 69 |
| 3.1.1 Electro -optic properties of semiconductor nano -cluster materials | 69 |
| 3.1.2 Electro -optic properties of electro -optic chromophores | 76 |
| 3.2 Measurements of Electro -optic Pockels and Kerr coefficients | 81 |
| 3.2.1 Linear electro -optic coefficient measurement by ellipsometric setup | 83 |
| 3.2.2 Linear Electro -optic coefficient measurement by MZI setup | 88 |
| 3.2.3 Quadratic electro -optic coefficient measurement by ellipsometric setup | 91 |
| 3.3 Results and discussion | 95 |
| 3.3.1 Polymer matrix nano -cluster electro -optic films | 95 |
| 3.3.2 Polymeric electro -optic chromophore films | 116 |
| 3.4 Conclusions | 130 |
| 3.5 References | 131 |

| | |
|---|-----|
| Chapter 4. Application of Electro-optic Materials: Design of Polymeric Optical Modulators | 135 |
| 4.1 Introduction | 135 |
| 4.2 Waveguide analysis by means of effective index approach | 139 |
| 4.2.1 Minimum (cutoff) thickness of planar waveguide | 139 |
| 4.2.2 Channel (ridge) waveguide | 144 |
| 4.3 High speed operation and traveling wave electrode design | 148 |
| 4.3.1 High speed device | 148 |
| 4.3.2 Traveling wave electrode design | 154 |
| 4.4 Waveguide and electrode fabrication | 158 |
| 4.5 Conclusions | 159 |
| 4.6 References | 160 |
| Chapter 5. Conclusions | 162 |

List of Figures and Tables

| | |
|---|----|
| Fig.1 -1. Structure of MZI modulators: Basic cosine response of a MZI modulator. | 7 |
| Fig.1 -2. Power-length product as a function of switching speed of some electro-optic and nonlinear optical materials. | 9 |
| Fig.2 -1. Densities of states for 3D, 2D, 1D, and 0D systems. | 18 |
| Fig.2 -2. Enhanced confinement and oscillation strength in compressed excitons. | 20 |
| Table 2.1. Number of total atoms and percentage of surface atoms vary with radius of nano-clusters. | 21 |
| Fig.2 -3. Formation of surface capped semiconductor nano-crystals. | 23 |
| Fig.2 -4. ESA schematic for build up of multilayer assemblies by consecutive absorption of anionic and cationic molecule-based polyelectrolytes. | 27 |
| Fig.2 -5. ESA processing of polymers in combination with water-soluble nano-cluster quantum dots allows wide variation of thin-film properties. | 27 |
| Fig.2 -6. Needle coronapoling setup. (a) Configuration; (b) Picture of poling setup. | 30 |
| Fig.2 -7. Room temperature absorption spectra of CdS, CdSe and CdTe nano-crystallites with different particle sizes. (a): 2-3 nm diameter of CdSe, CdS, and CdTe nano-particles, (b): CdSe nano-particles at various sizes. | 32 |
| Fig.2 -8. Pictures of various films ready for measurements. | 35 |
| Fig.2 -9. Optical absorption spectrum of CdS nano-particles dispersed in pyridine. | 37 |

| | |
|---|----|
| Fig.2 -10.LuminescencespectrumofCdSsolution(CdSdispersedinpridine). | |
| Peak intensityisat526.6nm. | 37 |
| Fig.2 -11.OpticalabsorptionspectraofCdSefilmsandsolution. | 40 |
| Fig.2 -12.LuminescencespectraofCdSefilmsfabricatedbyspincoating andESA. | 40 |
| Fig2 -13.TEM(A)anddiffractionring(B)ofCdSnano-clusters. | 3 |
| Fig.2 -14.TEM(A)anddiffractionring(B)ofCdSenano-clusters. | 43 |
| Fig.2 -15. Calculatedabsorptionbandedgevarieswiththediameter ofCdSquantum dots. | 46 |
| Fig.2 -16. Calculatedthresholdwavelengthshiftvarieswiththediameter ofCdS quantumdots. | 46 |
| Fig. 2-17.Maximumabsorptionvarieswiththickness(numberoflayers) andexternal voltageofPS -119/PDDAfilmswithandwithout external electricalfield. | 49 |
| Fig.2 -18.Opticaldensityvarieswiththickness(numberoflayers)and externalvoltage ofPS -119/PDDAfilmswithandwithout externalelectricalfield. | 49 |
| Fig.2 -19.Peakwavelengthvarieswiththickness(numberoflayers)and external voltageofPS -119/PDDAfilmswithandwithoutexternal electricalfield. | 50 |
| Fig.2 -20.OpticalabsorptionspectraofPS -119/PAHfilmswithdifferent thickness (numberofbilayers). | 55 |
| Fig.2 -21.AbsorptionvarieswithnumberofbilayersofPS -119/PAHfilms | |

- at peak position. 55
- Fig. 2 -22. Optical absorption spectra of PS -119/PDDA films with different thickness (number of bilayers). 56
- Fig. 2 -23. Absorption varies with number of bilayers of PS -119/PDDA films at peak position. 56
- Fig. 2 -24. AFM diagram of PS -119/PAH film, 200 bilayers. 57
- Fig. 2 -25. AFM diagram of PS -119/PDDA film, 75 bilayers. 57
- Fig. 2 -26. Absorption spectrum versus number of bilayers, pH value of PDDA solution is 5.8. 58
- Fig. 2 -27. Absorption spectrum versus number of bilayers, pH value of PDDA solution is 11.5. 58
- Fig. 2 -28. Absorption varies with number of bilayers of CdSe/PDDA films at peak position (585 nm), pH value of PDDA solution is 5.8 and 11.5. 59
- Fig. 2 -29. XPS spectrum of CdSe -PDDA film made by ESA process, pH value of PDDA solution is 11.5, concentrations are: Cd=6.20, Se=2.08 (atomic %). 63
- Fig. 2 -30. XPS spectrum of CdSe -PDDA film made by ESA process, pH value of PDDA solution is 11.5, concentrations are compound Se=43.42, alloy Se=56.58 (atomic %). 64
- Fig. 2 -31. XPS spectrum of CdSe -PDDA film made by ESA process, pH value of PDDA solution is 5.8, concentration is Cd=6.14, Se=3.48 (atomic %). 64
- Fig. 3 -1. Relevant energy levels for SDGs (semiconductor nano -crystals dispersion in glasses) in the resonant regime. 73

| | |
|---|-----|
| Fig.3 -2.Schematicenergylevelschemediagramforthebulksemiconductor andfor themicro -crystallite. | 74 |
| Fig.3 -3.PlotsofIm $\chi^{(3)}$ andRe $\chi^{(3)}$ as a function of frequency, ω_0 is the resonance frequency. | 75 |
| Fig.3 -4.3kinds ofelectro -opticpolymers. | 79 |
| Fig.3 -5. Ellipsometricsetup. | 84 |
| Fig.3 -6.Pictureofellipsom etricsetup. | 85 |
| Fig.3 -7.Mach -Zehnderinterferometricsetupforlinearelectro -opticeffect measurements. | 94 |
| Fig.3 -8.PictureofMach -Zehnderinterferometricsetup. | 95 |
| Fig.3 -9.Modulationfrequencydependentofr r_{33}/r_{113} ratioofnano -cluster CdSe/PDDA ESAfilm. | 96 |
| Fig.3 -10.r r_{33} varies with modulation frequency of CdSe films fabricated at different conditions, poling voltage is 80 volts/micron. | 98 |
| Fig.3 -11.r r_{33} varies with poling voltage of spin coated CdSe films. | 104 |
| Fig.3 -12. r_{33} of CdSe/Nor -65 film versus CdSe concentration, poling voltage 80 volts/micron, modulation frequency 300 Hz. | 106 |
| Fig.3 -13.r r_{33} as a function of modulating frequency measured using the Mach-Zehnder setup. | 110 |
| Fig.3 -14.r r_{113} as a function of modulating frequency measured using the Mach-Zehnder setup. | 110 |
| Fig.3 -15.r r_{113} as a function of modulating frequency measured with the ellipsometric setup. | 115 |

| | | | |
|-------------|----------------------|---|-----|
| Fig.3 -16.r | 333asa | functionofmodulatingfrequency measuredwiththe ellipsometric setup. | 115 |
| Fig.3 -17. | | Molecularstructuresofvariouspolymersusedinthe present work. | 118 |
| Fig.3 -18. | | Modulationfrequencydependenceofr ₁₁₃ ofESACL D/PDDA film. | 119 |
| Fig.3 -19. | | Modulationfrequencydependenceofr ₃₃₃ ofESACL D/PDDA film. | 120 |
| Fig.3 -20. | | Modulationfrequencydependenceofr ₃₃₃ andr ₁₁₃ ofspincoating CLD/PDDA(wt.31%CLD)film. | 120 |
| Fig.3 -21.r | 333,r ₁₁₃ | varywithfrequencyofmodulationvoltageof PS-119/PDDA films. | 123 |
| Fig.3 -22.r | 333,r ₁₁₃ | varywithfrequencyofmodulationvoltageofproton irradiatedPS -119/PDDAfilms. | 123 |
| Fig.3 -23r | 333,r ₁₁₃ | varywithfrequencyofmodulationvoltageof PCBS/PDDAfilms. | 124 |
| Fig.3 -24.r | 333,r ₁₁₃ | varywithfrequency ofmodulationvoltageofproton irradiated PCBS119/PDDAfilms. | 124 |
| Fig.3 -25. | FT -IR | ofpolys -119/PDDAESAfilmswith(1 -A)andwithout (control-A) protonirradiation. | 125 |
| Fig.3 -26. | FT -IR | ofPCBS/PDDAESAfilmswith(3A)andwithout (control3)proton irradiation. | 125 |
| Fig.3 -27.r | 333 | ofPS -119/PDDAatdifferentthickness(240,378and540bilayers). | 126 |
| Fig.3 -28.r | 33,r ₁₃ | varywithpolingvoltageofPS -119/PDDA film(540bilayers), modulationfrequency1000Hz. | 127 |
| Fig.3 -29.r | 33 | varywithmodulatedfrequencyofBR/PDDA film. | 127 |

- Fig.3 -30.Electro -opticcoefficientofESABR/PDDAfilmsatdifferentthickness. 128
- Fig.3 -31.Electro -opticcoefficient ofPS -119/PDDAESAfilmsvarywith
 numberof bilayerswithandwithoutappliedfieldintheprocess
 offilmgrowth, modulationfrequencyis30Hz. 129
- Fig.4 -1.Schematicofchannelwaveguidestructure(lefthand)andatopview
 of wave-guidemultilayer(rightside). 136
- Fig.4 -2.Configurationofplanarwaveguide. 141
- Fig.4 -3.DispersioncurveofESAPS -119andCdSefilms. 142
- Fig.4 -4.Highfrequen cy(optical)dielectricconstantofESAPS -119
 andCdSefilms. 142
- Fig.4 -5.Cutoffthicknessofplanewaveguidevarieswithrefractiveinde x
 ofcore layer, $n_1=1, n_3=1.50$, wavelength=1550nm. 142
- Fig.4 -6.Cutoffthicknessofplanewaveguidevarieswithrefractiveindex
 ofcladding layer, $n_2=1.51$ and $1.61, n_3=1.50$,wa velength=1550nm.143
- Fig.4 -7.Configurationof3 -Dchannelwaveguid. 145
- Fig.4 -8.Effectiverefractiveindexversuscorelayerthickness. 145
- Fig.4 -9.Aspectratioasfunctionofnormalizedfrequencyof3 -Dchannel
 waveguide. 146
- Fig.4 -10.Ultrafastlaser spectroscopyofCdSenano -clusterdopedglass
 atdifferent pulseintensity. 149
- Fig.4 -11.Modulationindexasfunctionofmodulationlengthatdifferent
 modulation frequency, $n=1.51, n_m=1.56$. 152
- Fig.4 -12.Modulationindexasfunctionofmodulationlengthatdifferent
 $n_m, n=1.51, \omega_m=100\text{GHz}$. 152

| | |
|--|------|
| Fig.4 -13.Illustrationoftravelingwave. | 154 |
| Fig.4 -14. Effectivedielectricconstantasfunctionofelectrodesizes | .157 |
| Fig.4 -15. Characteristicimpedance asfunctionofelectrodesizes. | 157 |